



CS-03-015

March 9, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/759,671 01/16/04 |

Chyiu Huia Poon et al.

DUAL STEP SOURCE/DRAIN EXTENSION
JUNCTION ANNEAL TO REDUCE THE
JUNCTION DEPTH: MULTIPLE-PULSE LOW
ENERGY LASER ANNEAL COUPLED WITH
RAPID THERMAL ANNEAL

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on March 17, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date Stephen B. Ackerman 3/16/04

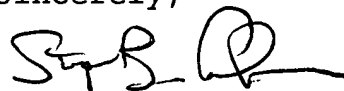
U.S. Patent 5,399,506 to Tsukamoto, "Semiconductor Fabricating Process," describes a process wherein shallow junction with reduced junction leakage is achieved by the combination of ion implantation and low temperature annealing (600 degrees C for 1 hour) to reduce point defects and pulsed laser (700 mJ/cm squared, 44 nsec pulse width) irradiation to activate the implanted ions.

U.S. Patent 5,937,325 to Ishida, "Formation of Low Resistivity Titanium Silicide Gates in Semiconductor Integrated Circuits," describes a process to form low resistance titanium silicide gates by using a laser anneal process in two steps.

U.S. Patent 6,100,171 to Ishida, "Reduction of Boron Penetration by Laser Anneal Removal of Fluorine," describes a laser annealing process for removing fluorine from a gate conductor and thereby reduce boron penetration.

U.S. Patent 6,365,476 to Talwar et al., "Laser Thermal Process for Fabricating Field-Effect Transistors," describes a process for fabricating a field-effect transistor semiconductor device using laser radiation.

Sincerely,

A handwritten signature in black ink, appearing to read 'S. B. Ackerman', with a stylized flourish at the end.

Stephen B. Ackerman,
Reg. No. 37761

Form PTO-1449

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several shouts if necessary)

Doc Ref Number (Optional)

CS-03-015

Lynchburg Museum

10 | 759,671

significant

Chyiu Hgia Poon et al.

Filing Date

01/16/04

Group Art Unit

U. S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

OTHER DOCUMENTS (Including Author, Title, Date, Portion or Pages, Etc.)

ОДНУМ

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.